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# EECS151 : Introduction to Digital Design and ICs

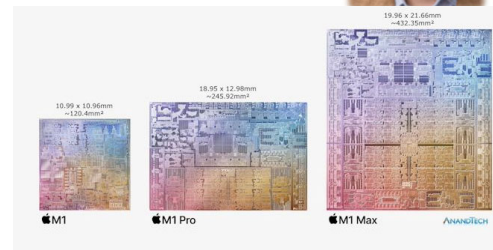
## Lecture 16 – Wires, Energy

Bora Nikolić



### Apple Announces M1 Pro & M1 Max: Giant New SoCs with All-Out Performance

October 18, 2021, AnandTech - The M1 Pro and Max both follow-up on last year's M1, Apple's first generation Mac silicon that ushered in the beginning of Apple's journey to replace x86 based chips with their own in-house designs. The M1 had been widely successful for Apple, showcasing fantastic performance at never-before-seen power efficiency in the laptop market. Although the M1 was fast, it was still a somewhat smaller SoC – still powering devices such as the iPad Pro line-up, and a corresponding lower TDP, naturally still losing out to larger more power-hungry chips from the competition.



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Anandtech.com

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## Review


- Two delay components in logical effort:
  - Parasitic delay ( $p$ )
  - Effort delay ( $F$ )
    - Logical effort ( $g$ ): intrinsic complexity of the gate
    - Electrical effort ( $h$ ): load capacitance dependent
- To minimize the delay all stages should have the same effort ( $h$ )
- Ideal effort is 4

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# Wires

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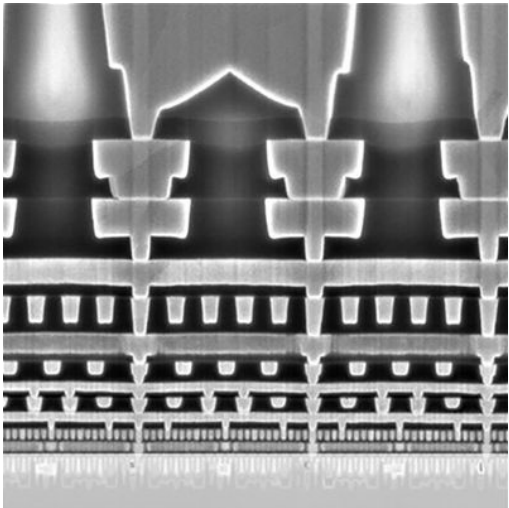
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## A modern technology is mostly wires

- Transistors are little things under the wires
- Many layers of wires
- Wires are as important as transistors
  - Speed and power



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## Wire Resistance

- $\rho$  = resistivity ( $\Omega \cdot \text{m}$ )

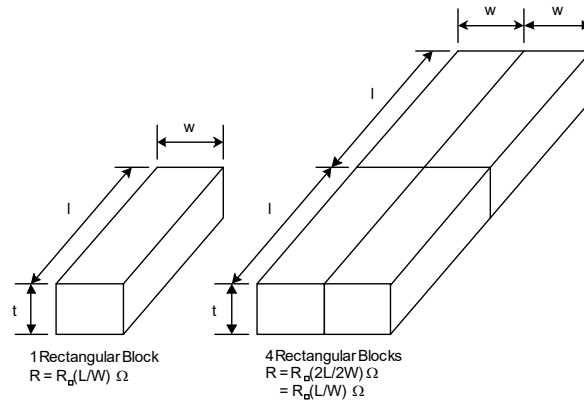
$$R = \frac{\rho}{t} \frac{l}{w} = R_{\square} \frac{l}{w}$$

- $R_{\square}$  = sheet resistance ( $\Omega/\square$ )

- $\square$  is a dimensionless unit(!)

- Count number of squares

- $R = R_{\square} * (\# \text{ of squares})$



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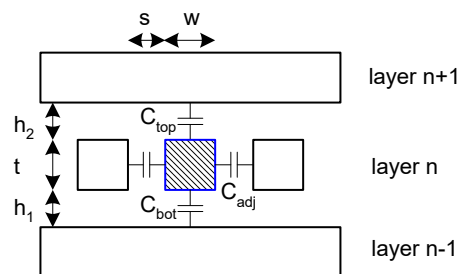
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## Wire Capacitance

- Wire has capacitance per unit length

- To neighbors
- To layers above and below

- $C_{\text{total}} = C_{\text{top}} + C_{\text{bot}} + 2C_{\text{adj}}$



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## Wire Delay

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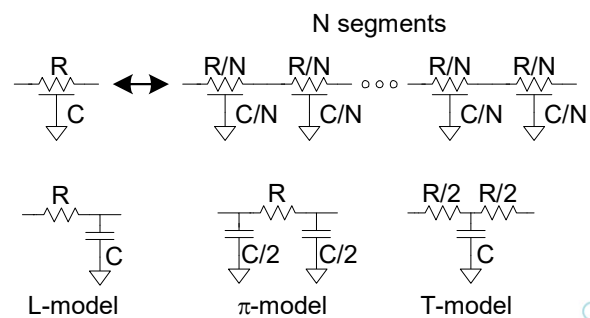
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## Wire RC Model

- Wires are a distributed system
  - Approximate with lumped element models
- 3-segment pi-model is accurate to 3% in simulation



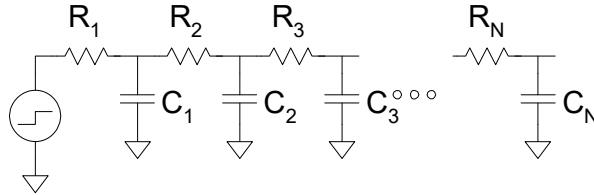
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## Elmore Delay for RC Tree



$$t_{pd} \approx \sum_{\text{nodes } i} R_{i \rightarrow \text{source}} C_i$$

$$= R_1 C_1 + (R_1 + R_2) C_2 + \dots + (R_1 + R_2 + \dots + R_N) C_N$$

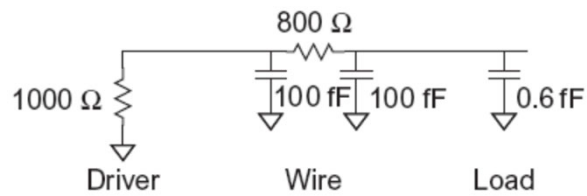
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## Example: RC Delay with Wire and Gate



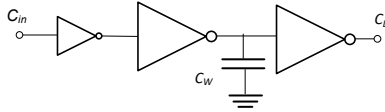
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## Logical Effort with Wires



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## Administrivia

- Homework 6 due this week
  - Homework 7 next week
- All labs need to be checked off by next week!
- Projects (ASIC and FPGA) start this week
- Midterm 2 is on November 4 at 7pm
- Courses:
  - EECS251B will be offered in Spring (pending Campus approval)
  - EE194/290C SoC Design

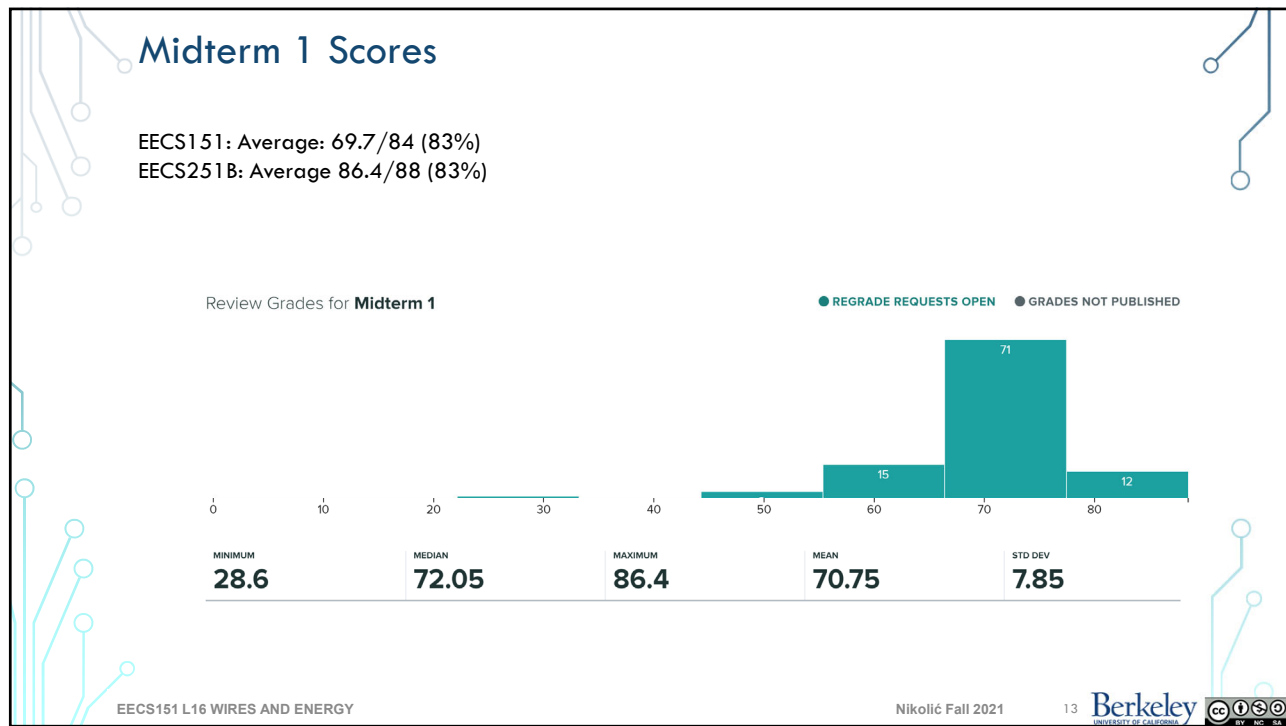
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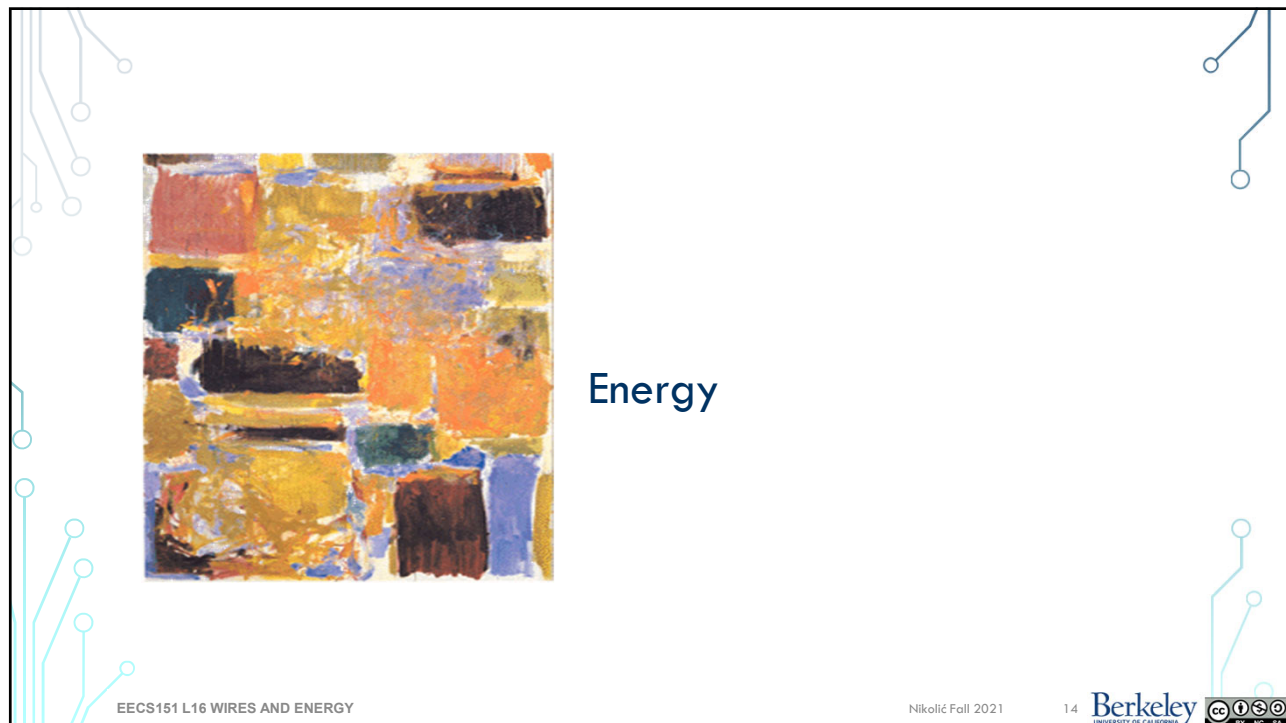
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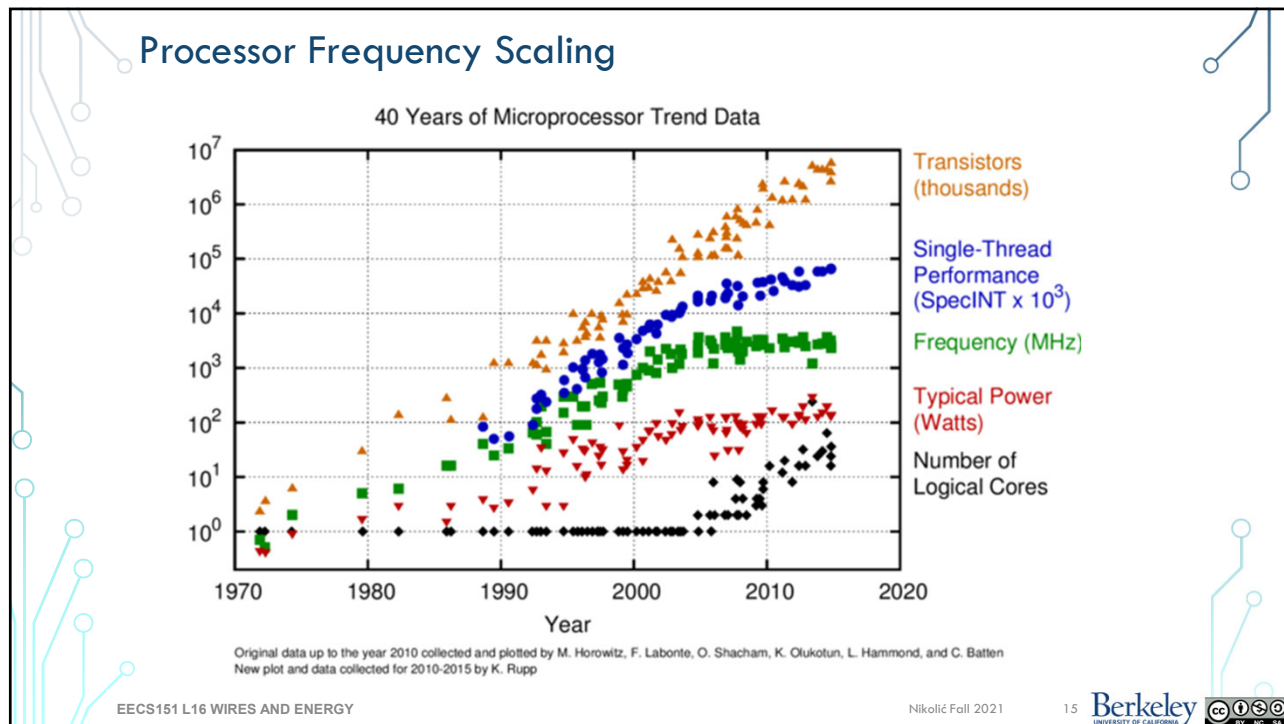
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## Power and Energy

- Power is drawn from a voltage source attached to the  $V_{DD}$  pin(s) of a chip.
- Instantaneous Power:  $P(t) = I(t)V(t)$
- Energy: 
$$E = \int_0^T P(t) dt$$
- Average Power: 
$$P_{\text{avg}} = \frac{E}{T} = \frac{1}{T} \int_0^T P(t) dt$$

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## Power in a Circuit Element

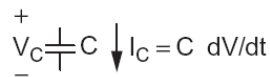
$$P_{VDD}(t) = I_{DD}(t)V_{DD}$$



$$P_R(t) = \frac{V_R^2(t)}{R} = I_R^2(t)R$$



$$\begin{aligned} E_C &= \int_0^\infty I(t)V(t)dt = \int_0^\infty C \frac{dV}{dt} V(t)dt \\ &= C \int_0^{V_C} V(t)dV = \frac{1}{2} CV_C^2 \end{aligned}$$



## Sources of Power Dissipation

- $P_{\text{total}} = P_{\text{dynamic}} + P_{\text{static}}$
- Dynamic power:  $P_{\text{dynamic}} = P_{\text{switching}} + P_{\text{shortcircuit}}$ 
  - Switching load capacitances
  - Short-circuit current
- Static power:  $P_{\text{static}} = (I_{\text{sub}} + I_{\text{gate}} + I_{\text{junct}} + I_{\text{contention}})V_{DD}$ 
  - Subthreshold leakage
  - Gate leakage
  - Junction leakage
  - Contention current



## Dynamic Power

## Charging and Discharging a Capacitor

- When the gate output rises
  - Energy stored in capacitor is  $E_C = \frac{1}{2} C_L V_{DD}^2$

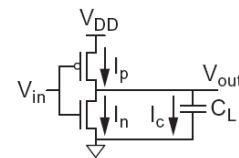
- But energy drawn from the supply is

$$E_{VDD} = \int_0^\infty I(t) V_{DD} dt = \int_0^\infty C_L \frac{dV}{dt} V_{DD} dt$$

$$= C_L V_{DD} \int_0^{V_{DD}} dV = C_L V_{DD}^2$$

- Half the energy from  $V_{DD}$  is dissipated in the pMOS transistor as heat, other half stored in capacitor

- When the gate output transitions HL
  - Energy in capacitor is dumped to GND
  - Dissipated as heat in the NMOS transistor



## Dynamic Power Reduction

How can we limit switching power?

- Try to minimize:

- Activity factor
- Capacitance
- Supply voltage
- Frequency

$$P_{\text{switching}} = \alpha C V_{DD}^2 f$$

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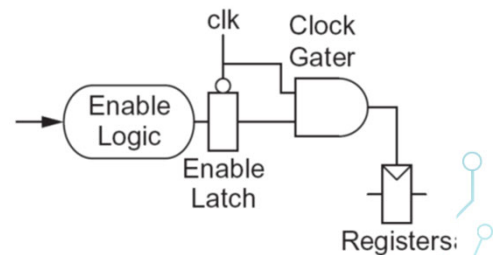
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## Reduce Activity Factor

- Clock gating
- The best way to reduce the activity is to turn off the clock to registers in unused blocks
  - Saves clock activity ( $\alpha = 1$ )
  - Eliminates all switching activity in the block
  - Requires determining if block will be used



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## Reduce Capacitance

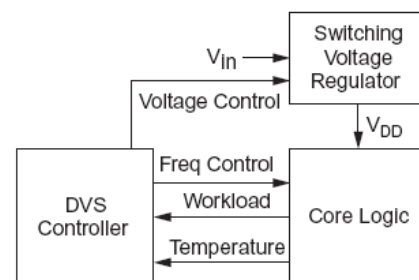
- Gate capacitance
  - Fewer stages of logic
  - Smaller gate sizes
- Wire capacitance
  - Good floorplanning to keep communicating blocks close to each other

$$P_{\text{switching}} = \alpha C V_{DD}^2 f$$

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## Reduce Voltage/Frequency

- Run each block at the lowest possible voltage and frequency that meets performance requirements
- Voltage domains
  - Provide separate supplies to different blocks
- Dynamic voltage/frequency scaling
  - Adjust  $V_{DD}$  and  $f$  according to workload



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## Leakage Power

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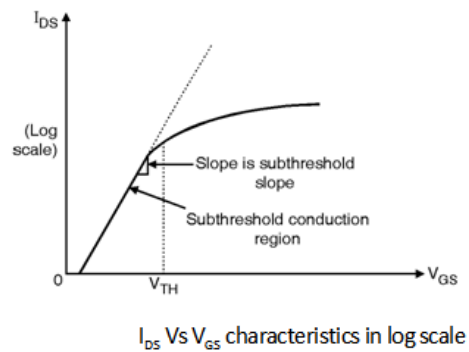
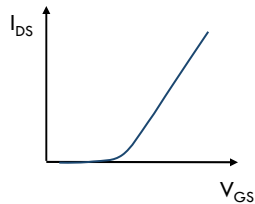
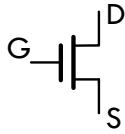
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## Subthreshold Leakage



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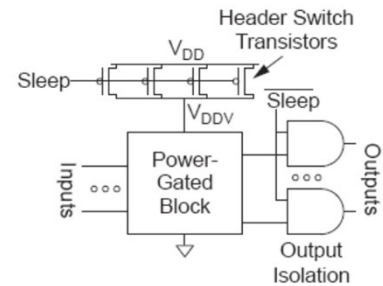
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## Power Gating

- Turn OFF power to blocks when they are idle to save leakage
  - Use virtual  $V_{DD}$  ( $V_{DDV}$ )
  - Gate outputs to prevent invalid logic levels to next block
- Voltage drop across sleep transistor degrades performance during normal operation
  - Size the transistor wide enough to minimize impact
- Switching wide sleep transistor costs dynamic power
  - Only justified when circuit sleeps long enough



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## Example: Power Management

- Power states

	C0 HFM	C0 LFM	C1/C2	C4	C6
Core Voltage					
Core Clock			OFF	OFF	OFF
PLL				OFF	OFF
L1 Caches			Flushed	Flushed	OFF
L2 Caches				Partial Flush	OFF
Wake-Up Time	active	active	$< 1 \mu s$	$< 30 \mu s$	$< 100 \mu s$
Power					

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## Summary

- Wire contributes to delay, especially in modern technology
- We can use RC model to capture wire delays
- Energy becomes an increasingly important optimization goal
  - Dynamic energy
  - Static energy